

Ordering number : ENN8155



SANYO Semiconductors

DATA SHEET

SCH2817 — General-Purpose Switching Device Applications

MOSFET : N-Channel Silicon MOSFET

SBD : Schottky Barrier Diode

Features

- Composite type with a N-Channel Silicon MOSFET (SCH1417) and a Schottky Barrier Diode (SS05015SH) contained in one package facilitating high-density mounting.
- [MOSFET]
 - Low ON-resistance.
 - Ultrahigh-speed switching.
 - 1.8V drive.
- [SBD]
 - Short reverse recovery time.
 - Low forward voltage.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V _{DSS}		15	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		1.6	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	6.4	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² ×0.8mm) 1unit	0.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	V _{RRM}		15	V
Nonrepetitive Peak Reverse Surge Voltage	V _{RSM}		15	V
Average Output Current	I _O		0.5	A
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	3	A
Junction Temperature	T _J		-55 to +125	°C
Storage Temperature	T _{stg}		-55 to +125	°C

Marking : QS

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SCH2817

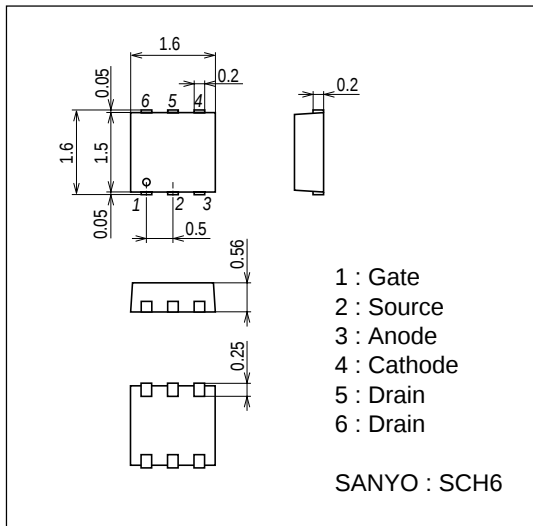
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	15			V
Zero-Gate Voltage Drain Current	IDSS	VDS=15V, VGS=0			1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	VDS=10V, ID=800mA	1.38	2.3		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=800mA, VGS=4V		120	160	mΩ
	RDS(on)2	ID=400mA, VGS=2.5V		165	240	mΩ
	RDS(on)3	ID=100mA, VGS=1.8V		230	350	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		105		pF
Output Capacitance	Coss	VDS=10V, f=1MHz		30		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		24		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		7.8		ns
Rise Time	tr	See specified Test Circuit.		27		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		18		ns
Fall Time	tf	See specified Test Circuit.		22		ns
Total Gate Charge	Qg	VDS=10V, VGS=4V, ID=1.6A		1.86		nC
Gate-to-Source Charge	Qgs	VDS=10V, VGS=4V, ID=1.6A		0.33		nC
Gate-to-Drain “Miller” Charge	Qgd	VDS=10V, VGS=4V, ID=1.6A		0.55		nC
Diode Forward Voltage	VSD	IS=1.6A, VGS=0		0.87	1.2	V
[SBD]						
Reverse Voltage	VR	IR=0.5mA	15			V
Forward Voltage	VF	IF=0.5A		0.4	0.46	V
Reverse Current	IR	VR=6V			90	μA
Interterminal Capacitance	C	VR=10V, f=1MHz		13		pF
Reverse Recovery Time	trr	IF=IR=100mA, See specified Test Circuit.			10	ns

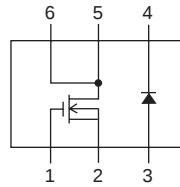
Package Dimensions

unit : mm

2230A



Electrical Connection



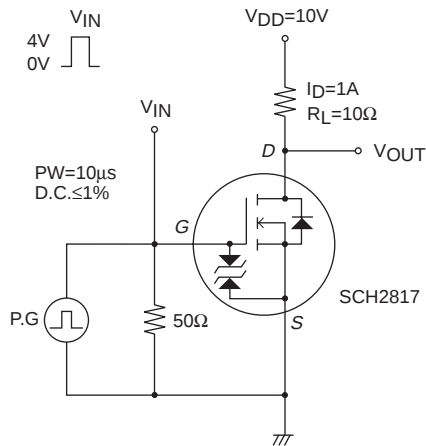
1 : Gate
2 : Source
3 : Anode
4 : Cathode
5 : Drain
6 : Drain

Top view

SCH2817

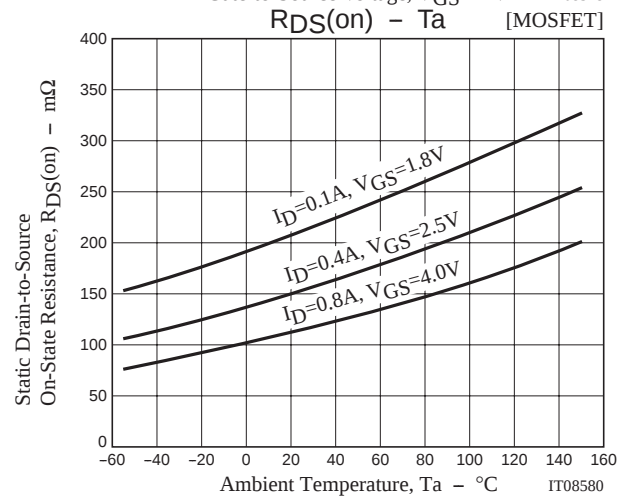
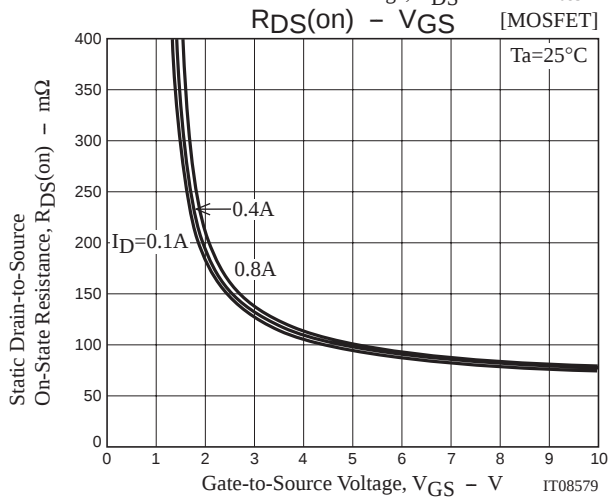
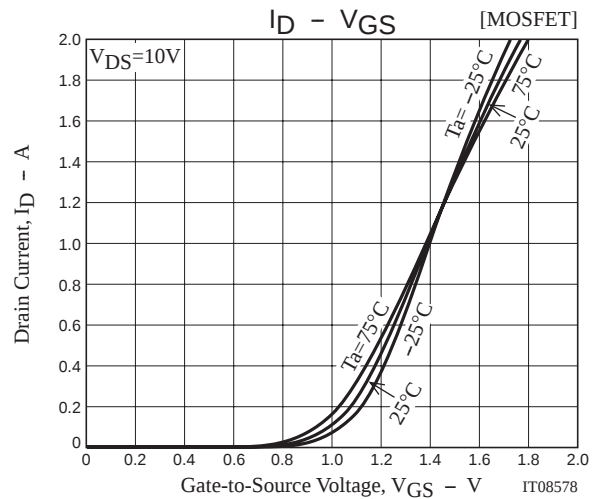
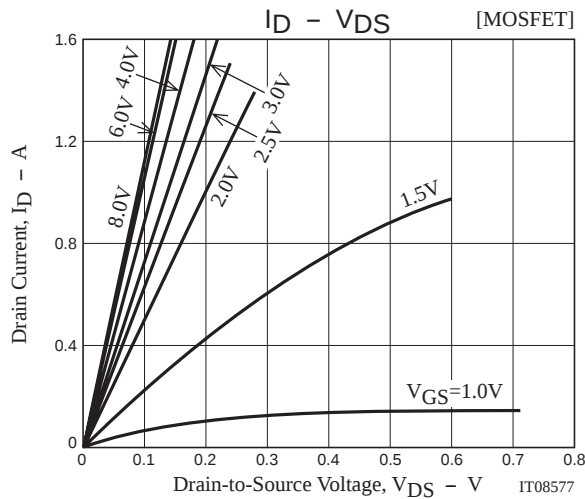
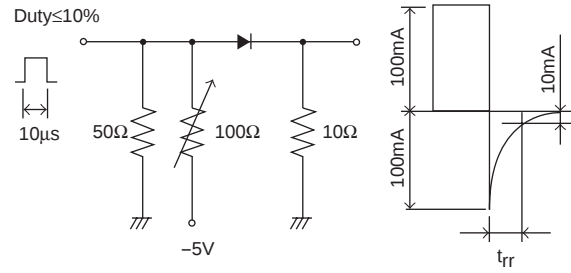
Switching Time Test Circuit

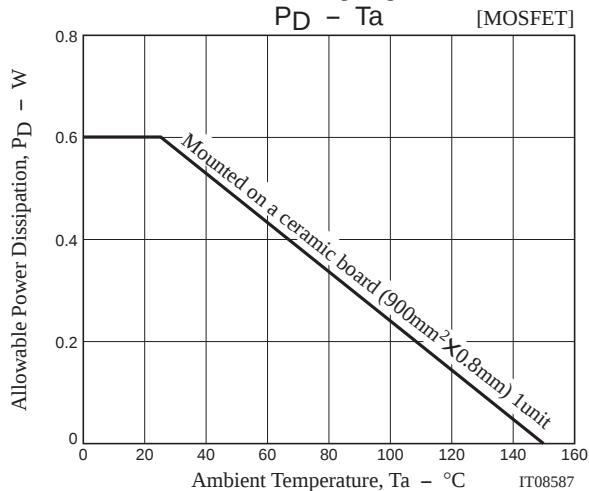
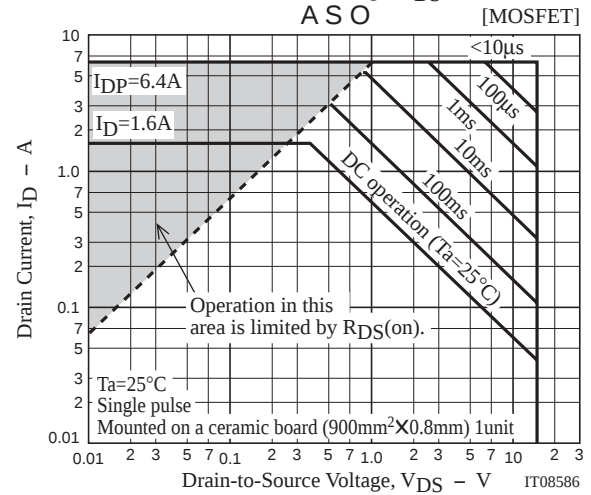
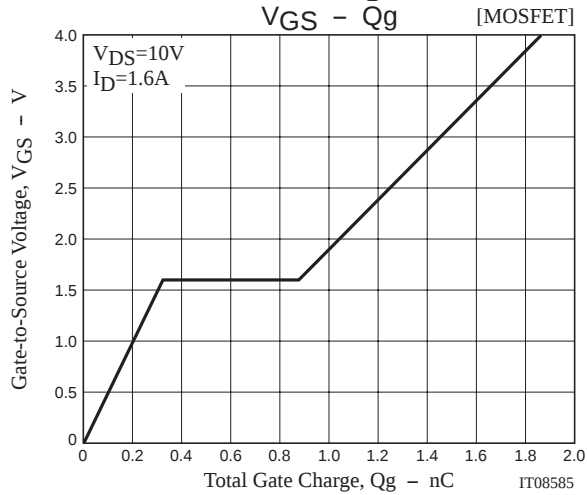
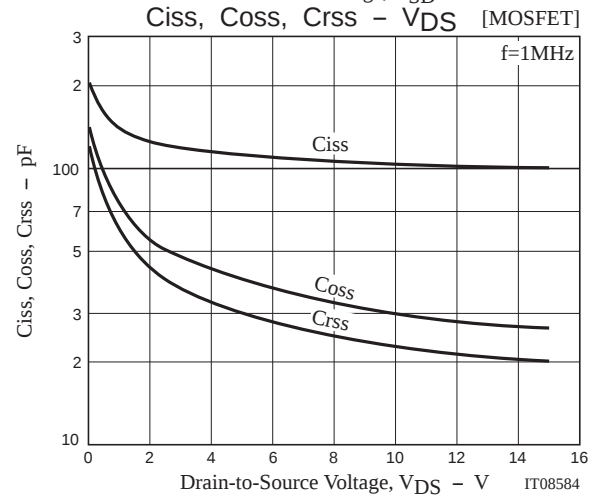
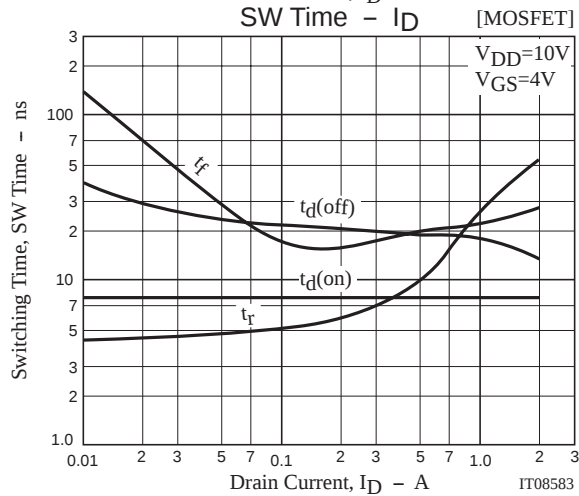
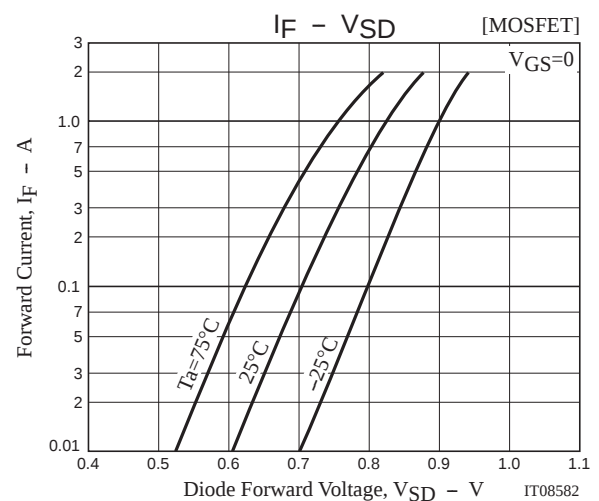
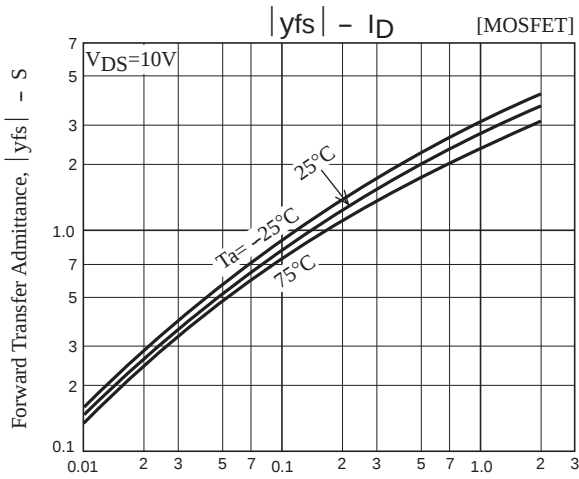
[MOSFET]

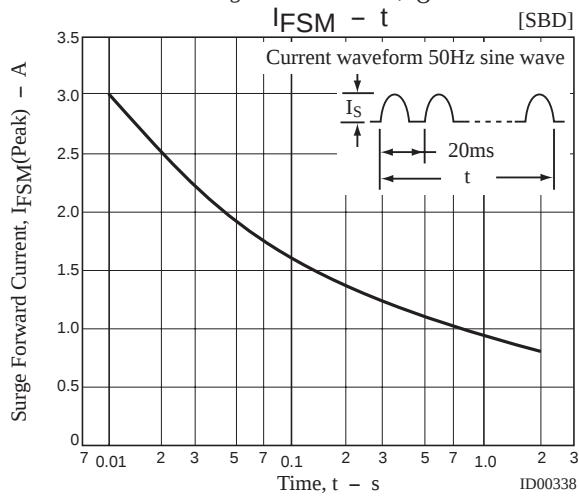
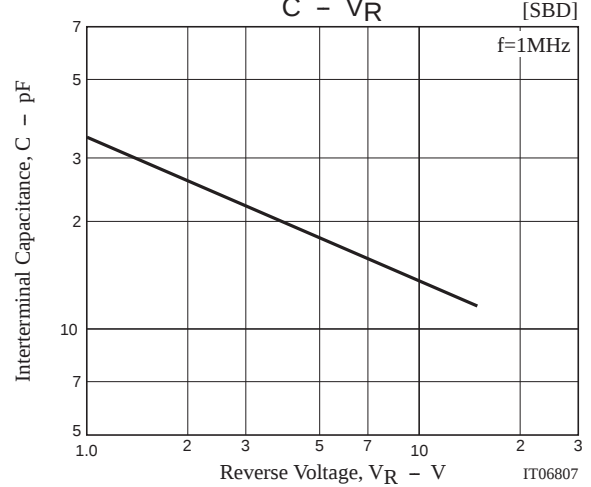
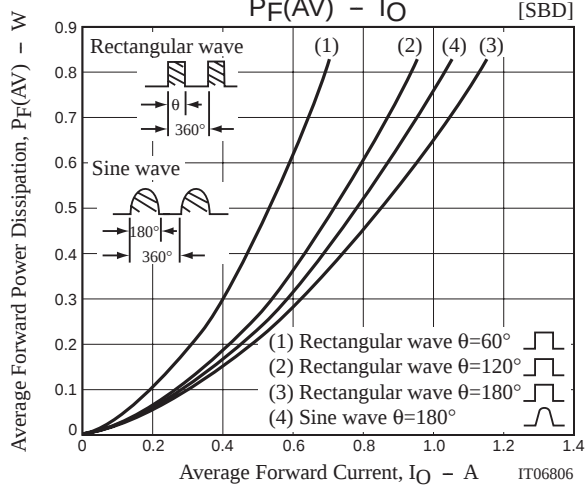
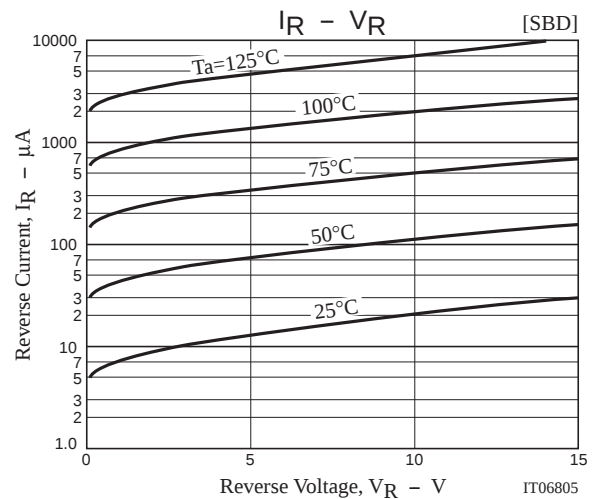
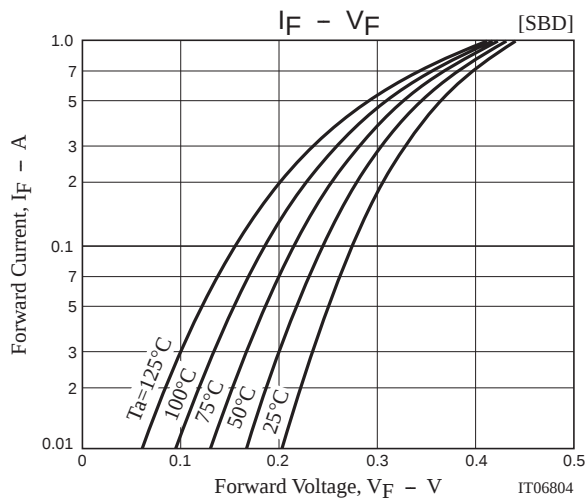


t_{rr} Test Circuit

[SBD]







Note on usage : Since the SCH2817 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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